

# CCD And Readout Electronics



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# Outline



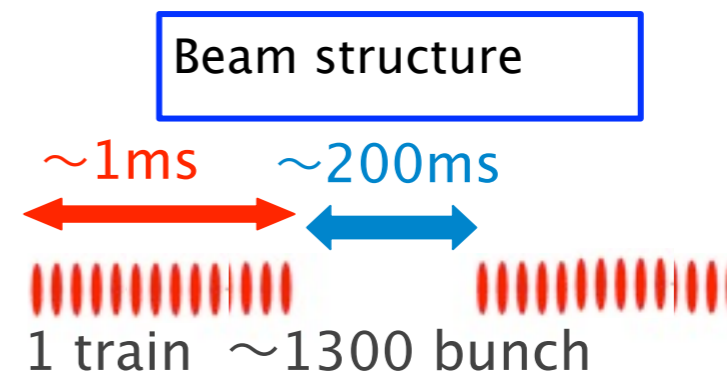
- FPCCD
- CCD and ASIC Prototypes
- Test Systems
- Results



- **Vertex detector**

- high impact parameter resolution ( near interaction point)
- accurate tagging (pixel occupancy  $\sim 1\%$ )

Finely segmented pixel is required.



- **FPCCD (Fine Pixel CCD) vertex detector.**

- pixel size  $5 \times 5 \mu\text{m}^2$  (high position resolution)
- fully depleted epi layer :  $15 \mu\text{m}$ , Si total  $50 \mu\text{m}$  (high two track separation)
- total number of pixel :  $1.6 \times 10^{10}$  (high speed readout)
- inter train readout (no beam induced RF noise)

For FPCCD we need to develop CCD and ASIC.



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# CCD and ASIC Prototypes



# CCD and Readout ASIC Requirements



- Readout speed > 10MPix/sec

- using two 5MPix/sec in parallel

- Signal measurement accuracy < 50 e-

- faint signal level ~500 e-

- noise + analog to digital conversion accuracy < 50 e-

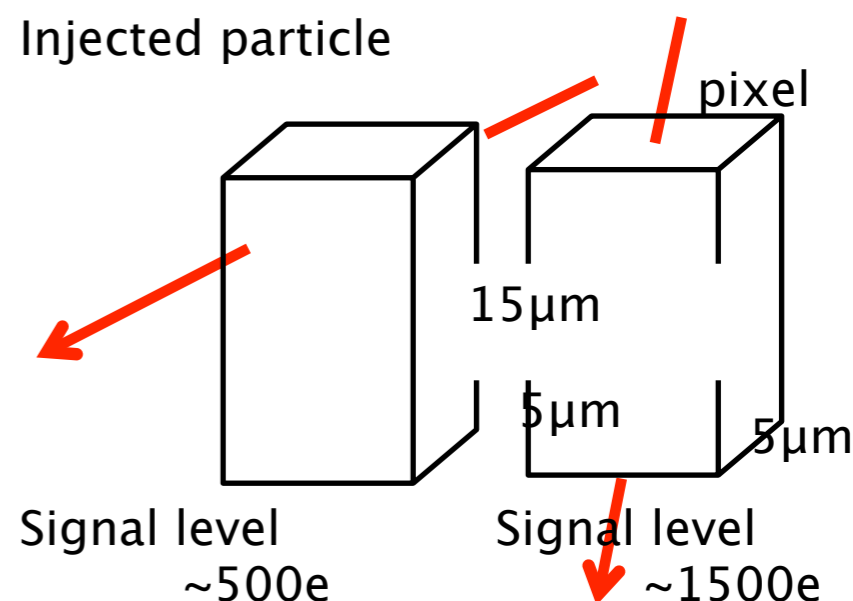
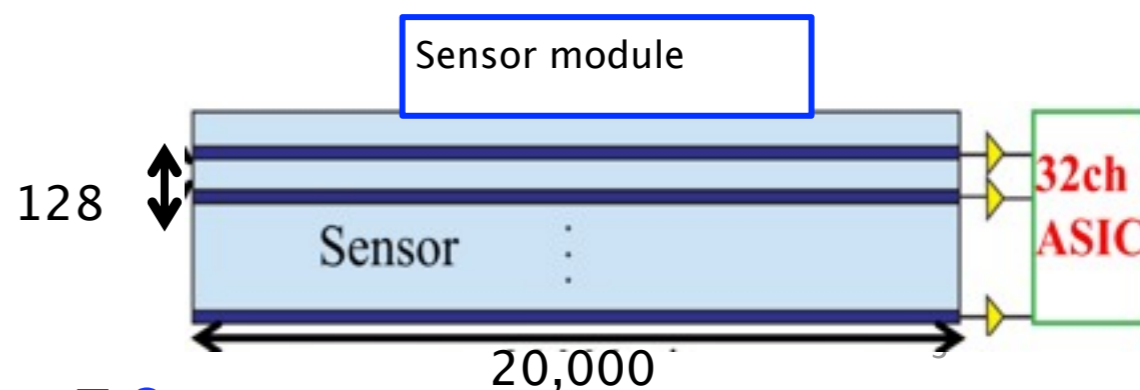
- Power consumption

- for ASIC < 6mW/ch

- for CCD < 10mW/ch

- placed in -40°C cryostat

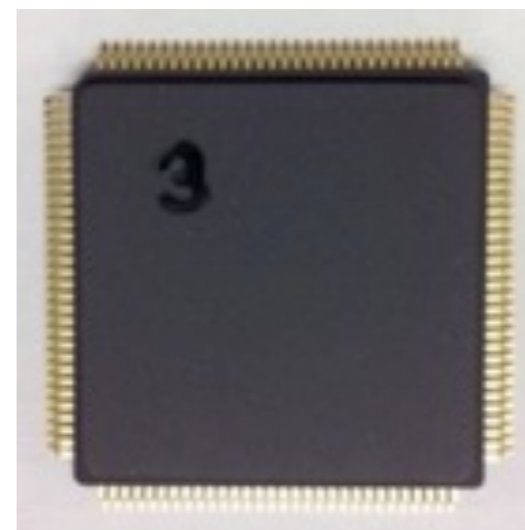
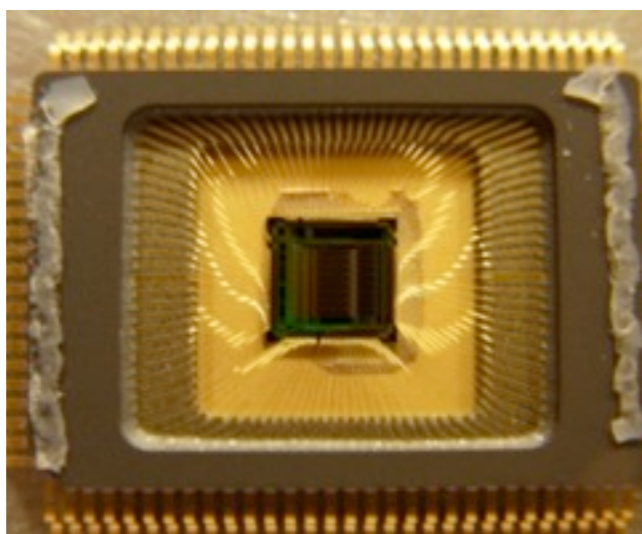
- total power consumption < 100W



CCD and ASIC designed should have these features.

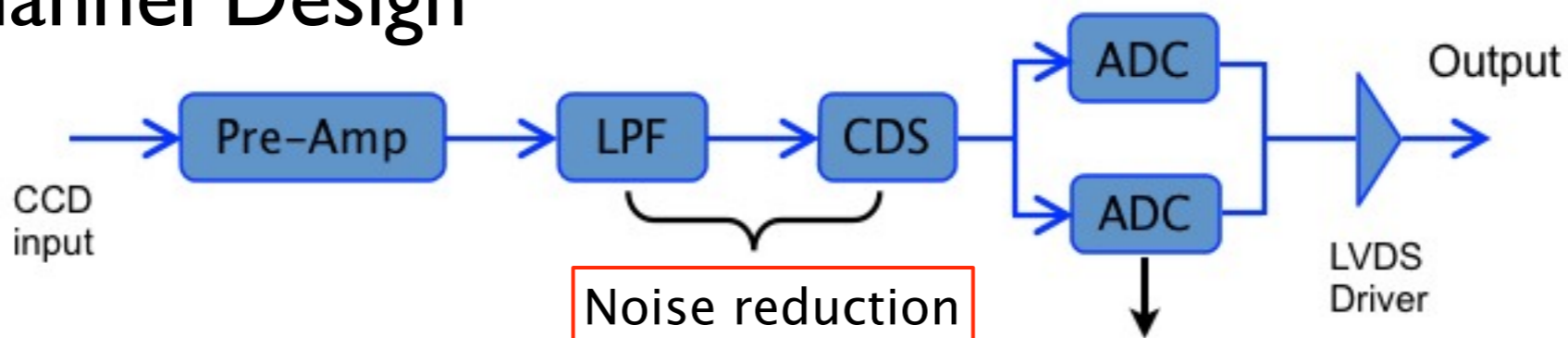


# ASIC Prototype



Chip parameters	2 <sup>nd</sup> prototype	3 <sup>rd</sup> prototype
process	0.35um	0.25um
Chip area	4.3x4.3mm <sup>2</sup>	3.7x3.75mm <sup>2</sup>
Gain coverage(from CCD)	12.5~200 (8 steps)	32~64(2 steps)
# of channels	8ch	8ch
Input capacitance form CCD	20pF	3.2pF

## Channel Design







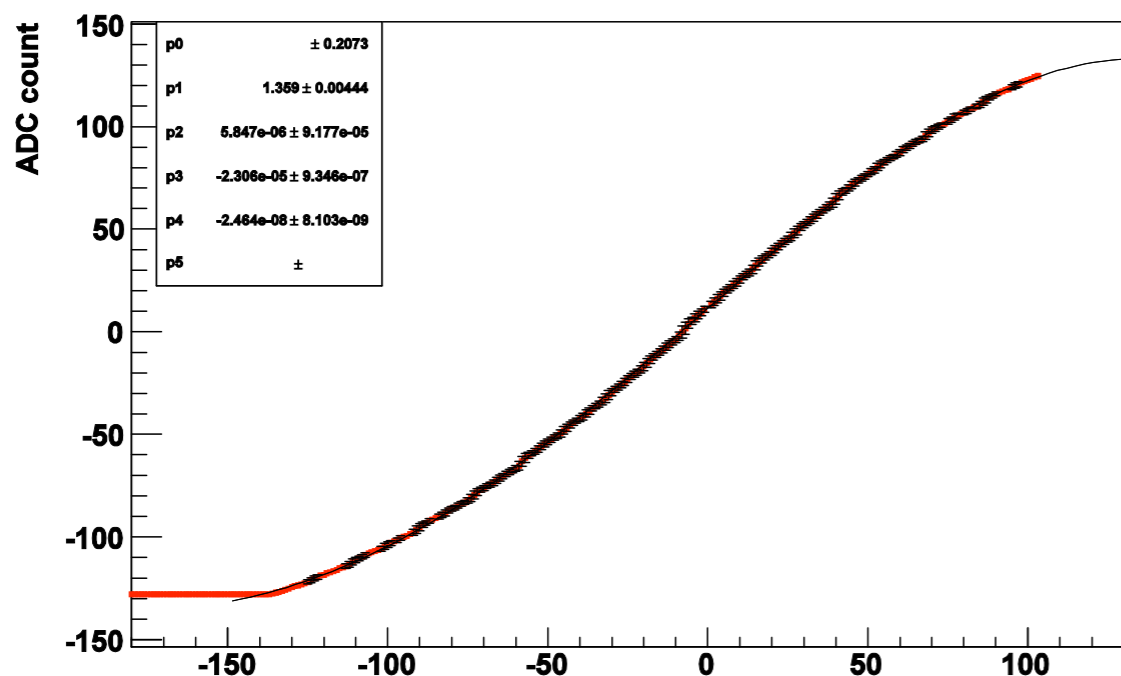
# ASIC Features And Improvements



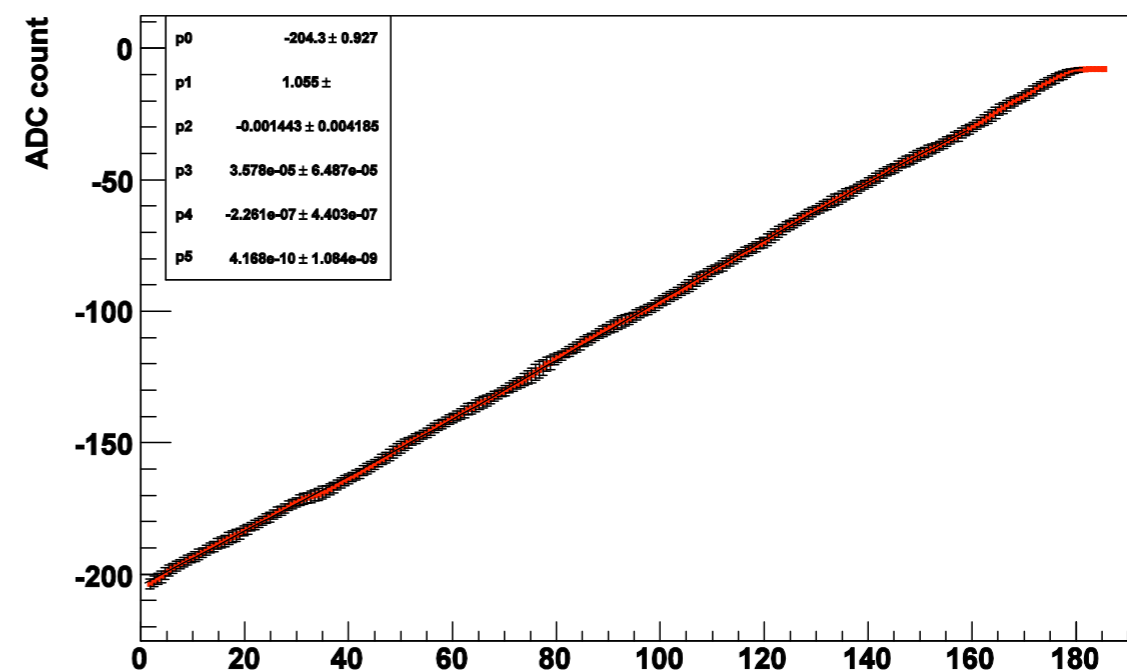
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- **Power consumption**
  - improved : 30.6 mW/ch -> 5.8 mW/ch
- **INL (Integral non linearity)**
  - Showed curvatures in linearity.
  - Caused upstream circuits.
  - improved : 17% -> < 2%

## 2nd Prototype



## 3rd Prototype





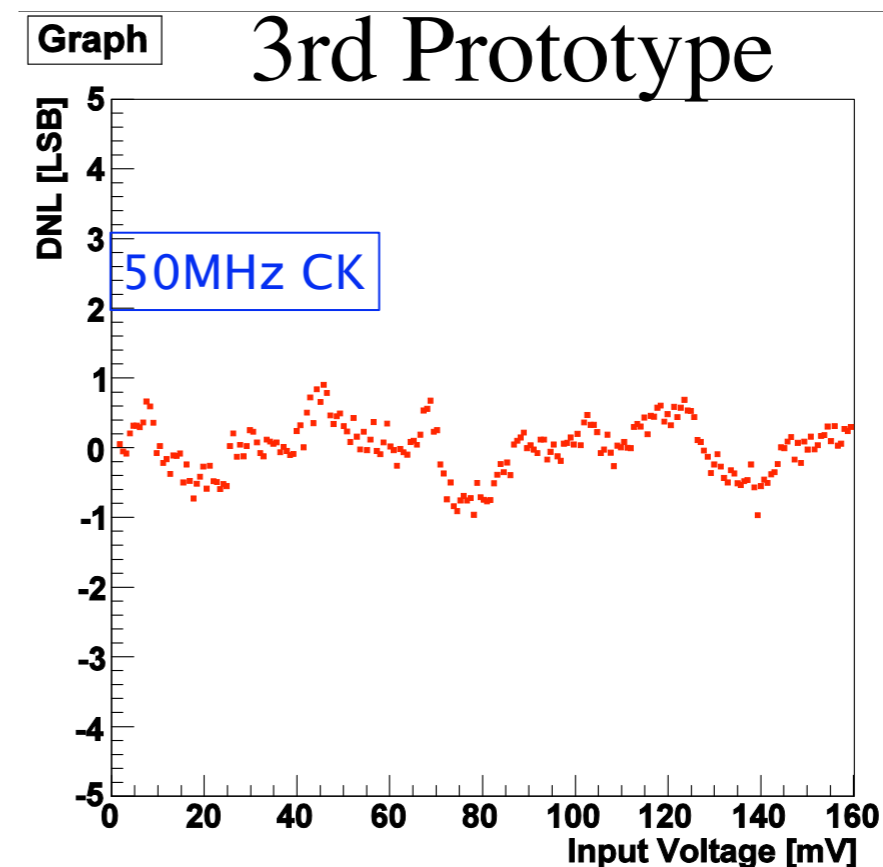
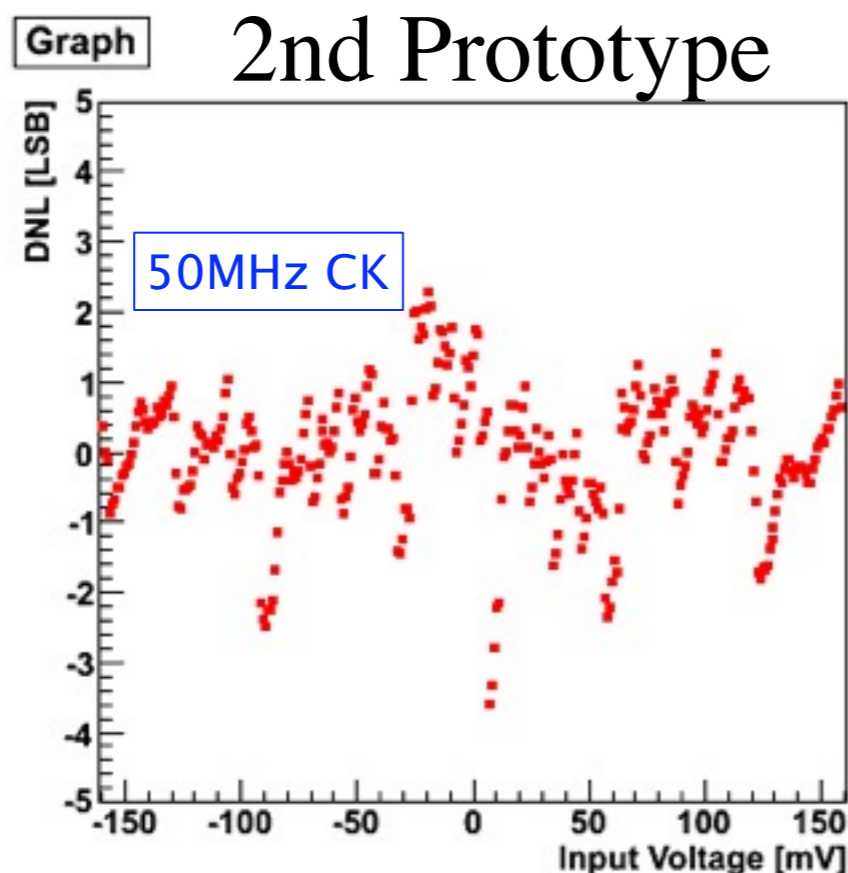
- Radiation tolerance

- 3rd prototype implemented DICE-FF radiation hardened by design flip-flop with high single event effect (SEE) immunity.

- DNL (Differential non linearity)

- due to displacement from bit weight it becomes meta-stable at bit change. Thus causes bit jump at higher frequencies.

- improves in 3rd prototype.





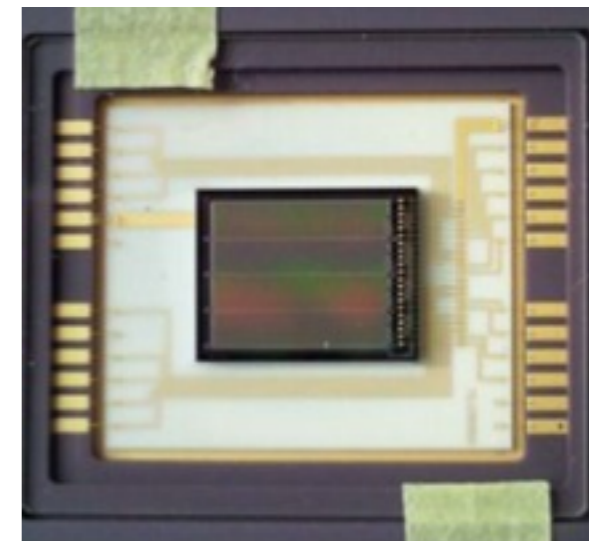


## Hamamatsu Photonics two phase transfer CCD

- Pixel size 12um x 12um

- chip size : 8.2mm(H) x 7.5mm(V)
  - thickness : epi layer 15um, Si total 50um
  - number of channels : 4
- has been tested.

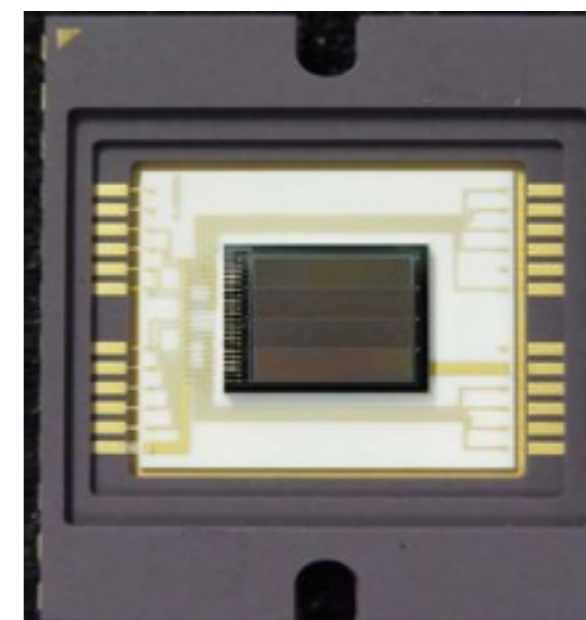
12 x 12 um



- Pixel size 6um x 6um

- horizontal shift register size : 6umx12um
  - thickness : epi layer 15um, Si total 50um
  - number of channels : 4
- test is going on.

6 x 6 um





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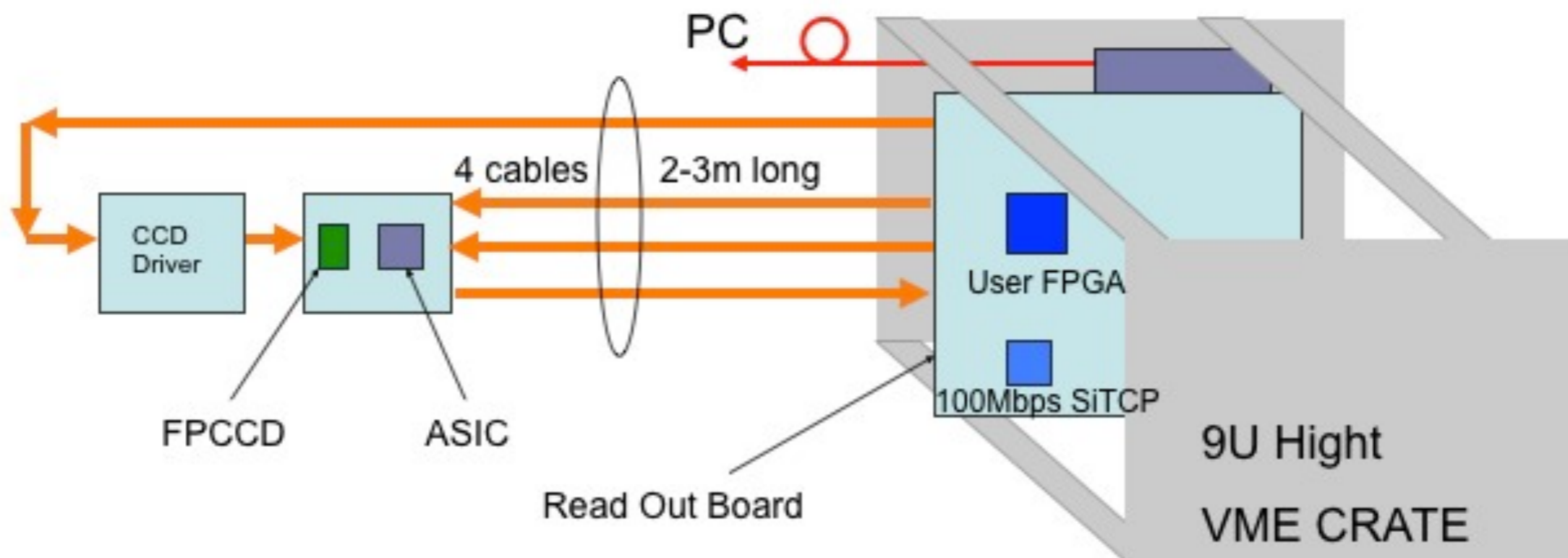
# Test Systems



# Previous VME Based Test System



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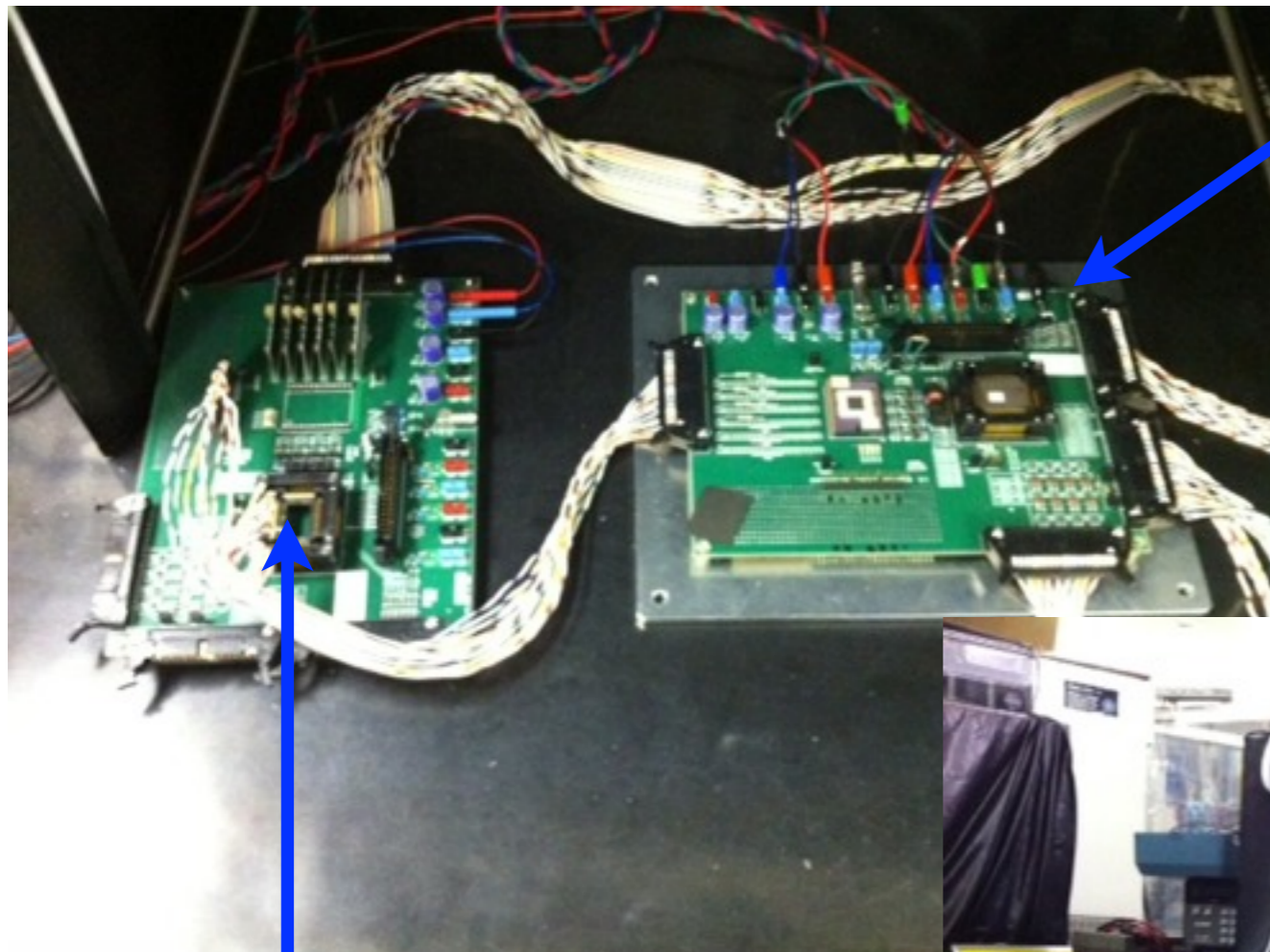


- 9U Read Out Board (ROB) : too large, especially for Beam Test
- Long cables : not easy to detect series of 3 nsec width ADC output pulses
- 100Mbps SiTCP : too small data rate (planned to change to 1GbE)
- Limited number of ROB and VME crate : 2 sites (Tohoku Univ., KEK)





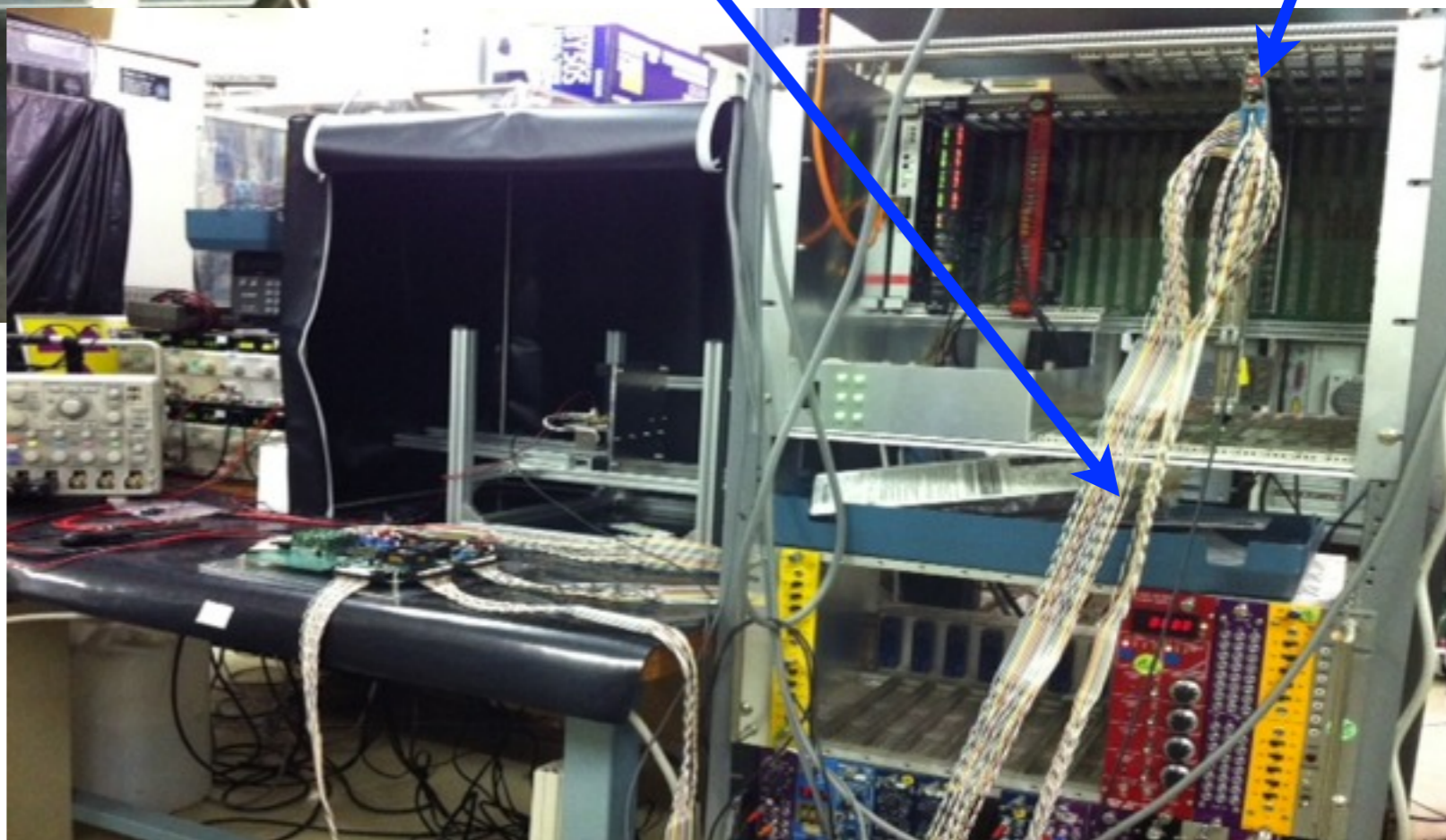
# Previous VME Based Test System



CCD, ASIC test board

One of the long cables

ROB

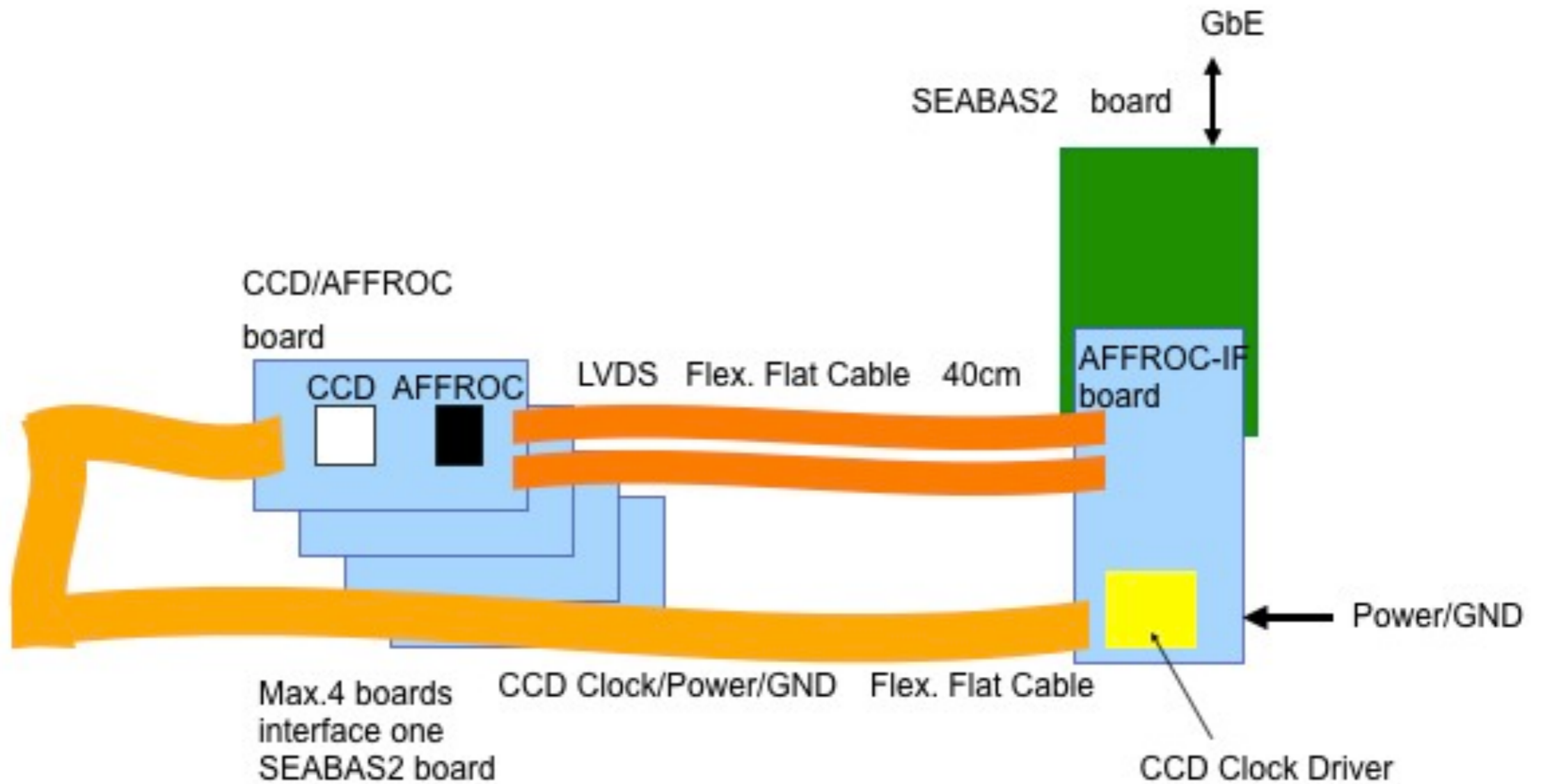


Another CCD,ASIC test board dedicated for CCD drivers



## SEABAS2 Based AFFROC Test System

AFFROC : Name of the 3<sup>rd</sup> ASIC







## Features

- Employ SEABAS2 (1GbE, ADC and DAC on board, compact size)
- Shorter and less cables (FFC support LVDS spec.)
  - Reliable operation at 100MHz or higher frequency can be expected by this LVDS cable and AFFROC new feature.
- On board DAC and ADC support automatic testing and self-diagnostics
  - example: AFFROC linearity test will be automated by using on-board DAC and AFFROC new feature.
- SEABAS1 available for early development of test circuits and programs
- Compact to support Beam Test.
- Additional site: Shinshu University.





# SEABAS2 Based AFFROC Test System



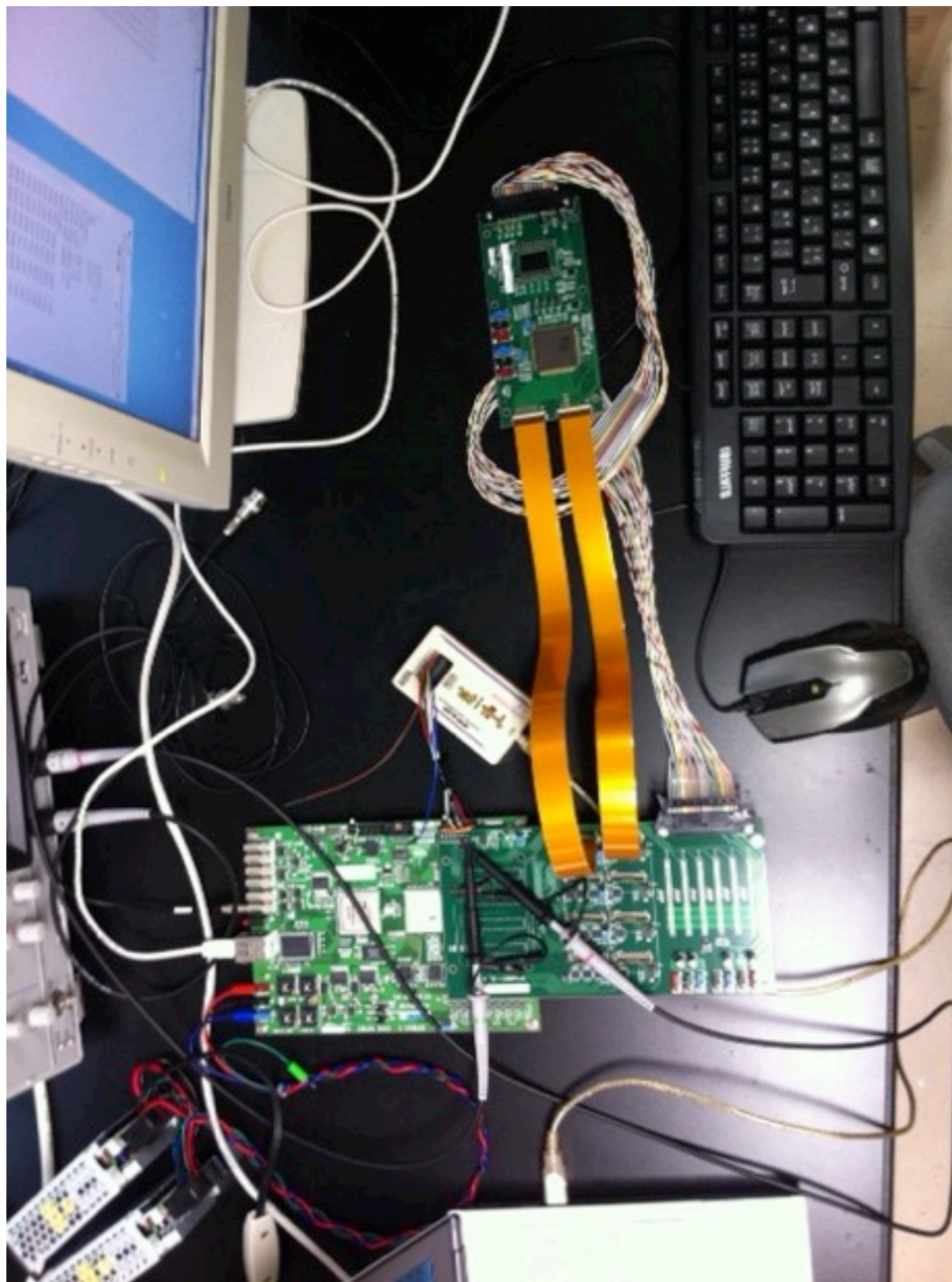
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- Employing SEABAS2 saves our development man power and cost.
- User FPGA + SiTCP structure is the same as the previous VME base ROB.
- Most of the logic circuits in the previous test system can migrate to the new User FPGA of SEABAS2 board.
  - Previous User FPGA : Xilinx Spartan 3A family “XC3S700A”  
1,472 CLB 360Kbit RAM
  - SEABAS2 User FPGA: Xilinx Vertex 5 family “XC5VLX50”  
7,200 CLB 2,160Kbit RAM
- Logic circuits to support four AFFROC may fit in one SEABAS2 board.
- We will buy 3 SEABAS2 boards at Tohoku. One of them is for SOI but we can use them as multi-SEABAS2 system for beam test to check position resolution and efficiency.
- 1GbE is still bottle neck, to support four CCD+AFFROC, so we need some data compression technology. Or we have multi-SEABAS2 board option.



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# SEABAS2 Based AFFROC Test System





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# 12 um CCD Test With ASIC Prototype 2



# Fe55 X-ray Measurements



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## ● CCD ( Hamamatsu Photonics)

- 12 x 12  $\mu\text{m}^2$
- thickness epi layer 15  $\mu\text{m}$ , Si total 50  $\mu\text{m}$

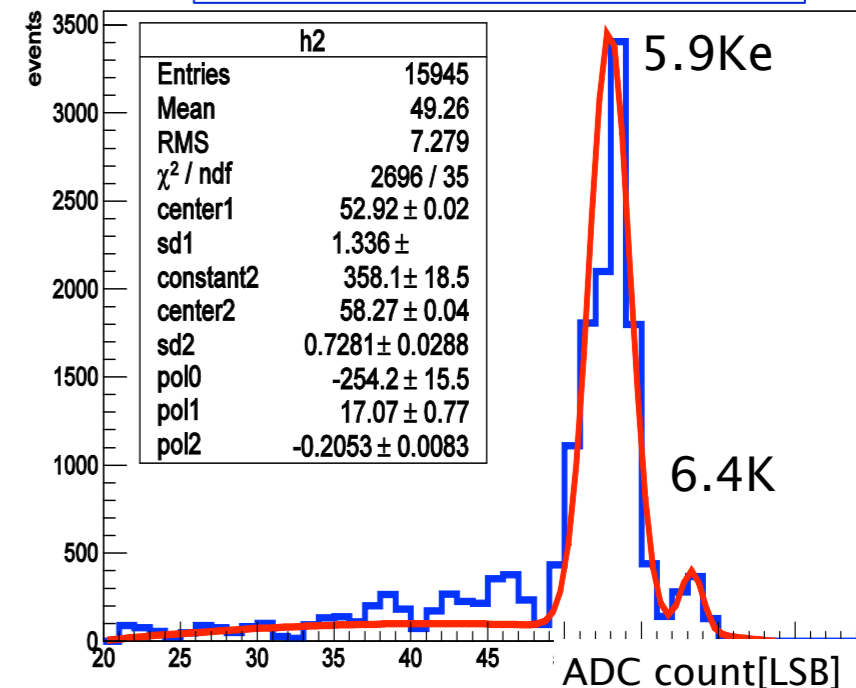
## ● Setup

- irradiation time 10s,  $-40^\circ\text{C}$
- 25 MHz ASIC operation clock
- S/N = 37 (single pixel hit extraction)
- energy resolution 120 eV

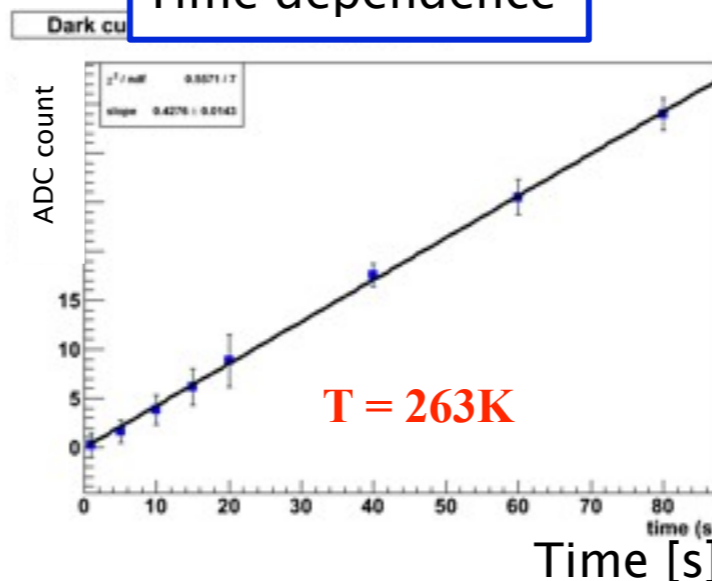
## ● Pedestal

- In ILC conditions (200ms and  $-40^\circ\text{C}$ ) dark current mainly suppressed.
- Noise 55 e (from CCD readout)

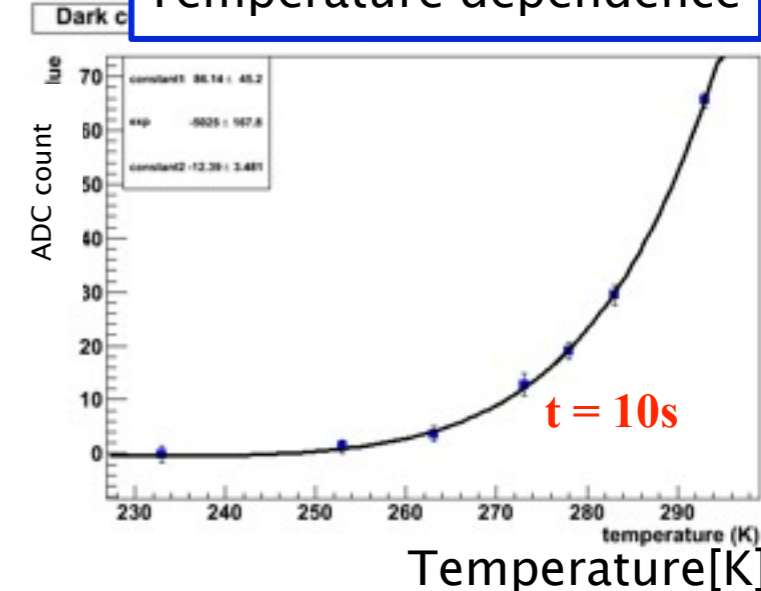
Fe55 spectrum



Time dependence



Temperature dependence







# Sr90 $\beta$ -ray Measurements



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- CCD ( Hamamatsu Photonics)

  - 12 x 12  $\mu\text{m}^2$

  - thickness epi layer 15  $\mu\text{m}$ , Si total 50  $\mu\text{m}$

- Setup

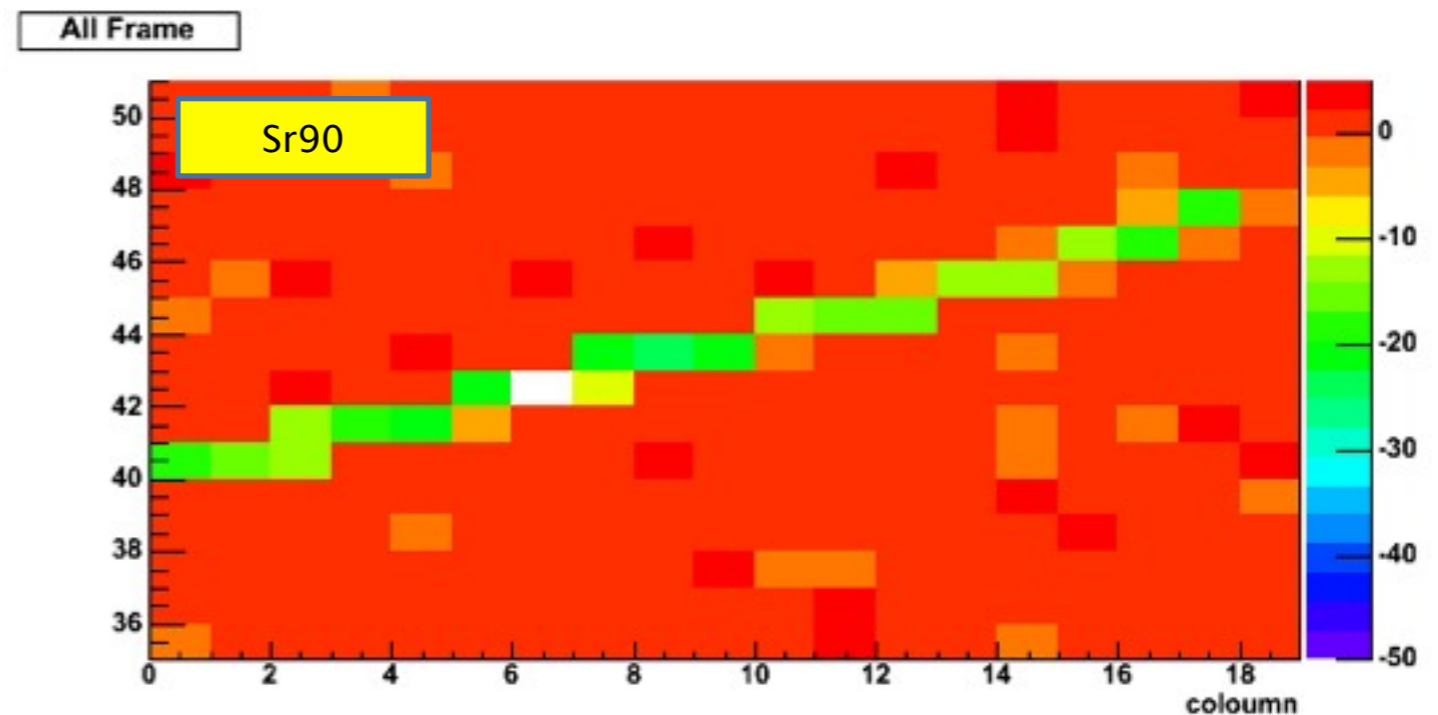
  - irradiation unit : 2 MeV  $\beta$  ray

  - Sr90 :  $\sim 10^\circ\text{C}$ , 2.5MPix/sec

- Sr90

  - checked charge distribution with 2MeV  $\beta$ -ray.

  - negligible charge leakage to adjacent pixels.





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# Tests with New ASIC i.e. AFFROC





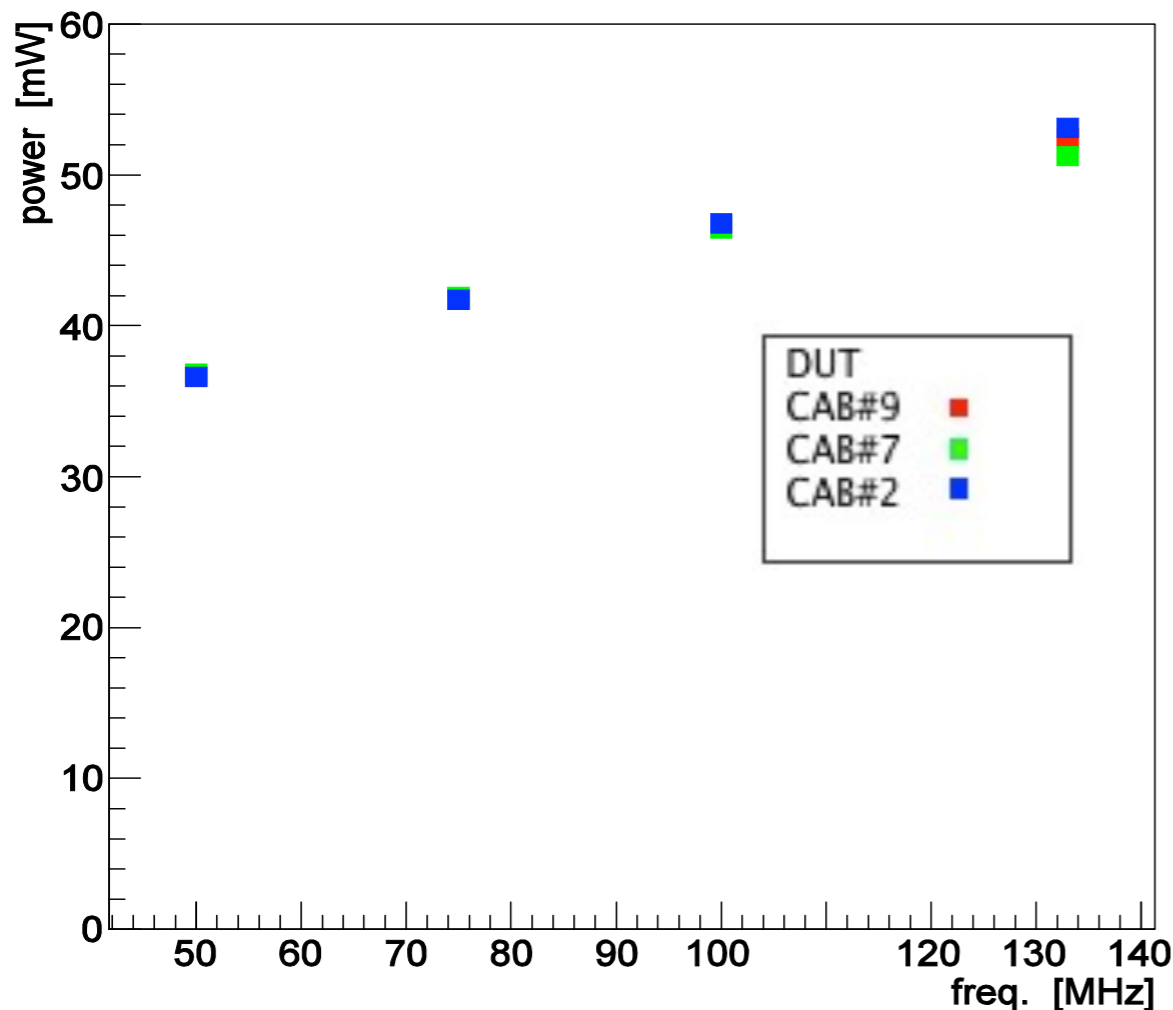
# Power Consumption



Hisao Sato

Power consumption at frequencies 50/75/100/133 MHz  
 $V_{dd}, V_{dd1} = 1.25V$   $V_{ss}, V_{ss1} = -1.25V$

freq. vs power



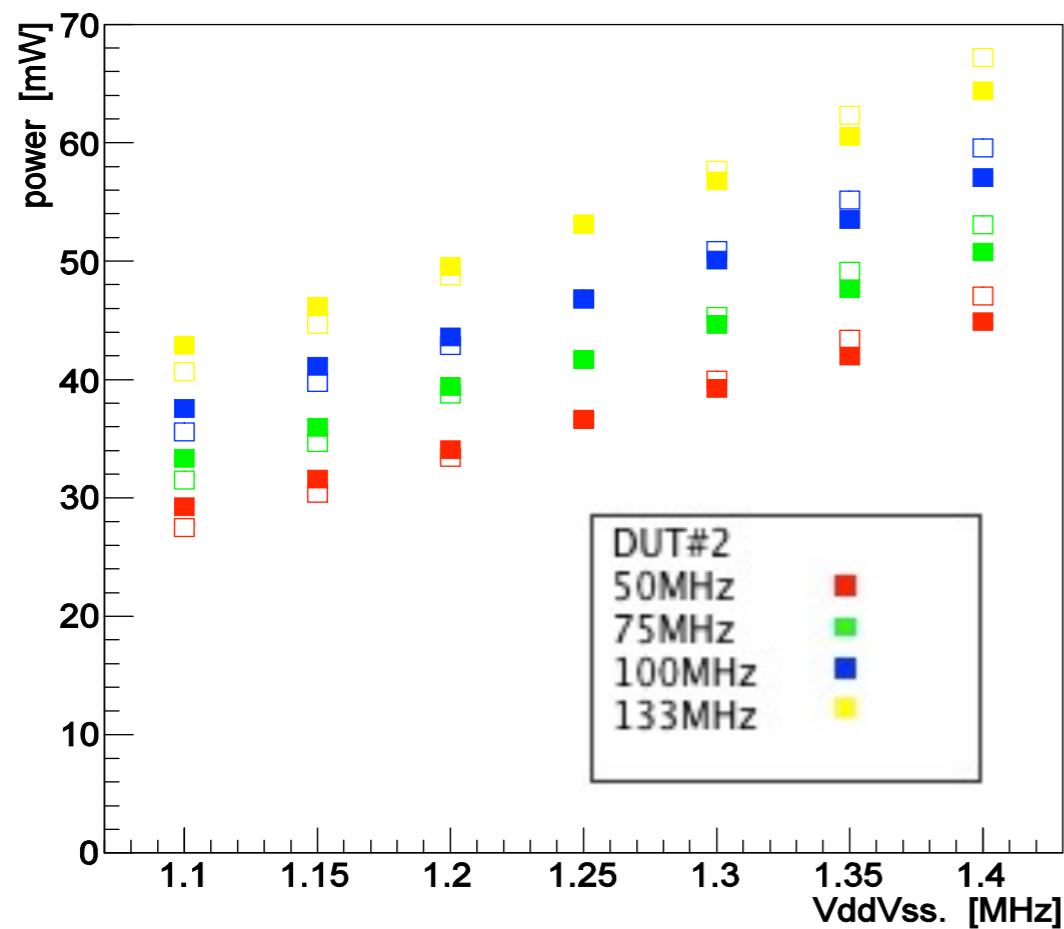
$P < 6mW/ch$  (48mW/chip)

One of major goal of AFFROC was power consumption. Target was to achieve  $< 6mW/ch$ . Achieved.



## Power consumption dependency to Vdd, Vss

VddVss. vs power



Power consumption dependency on Vdd, Vss as well on frequency looks reasonable.



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# Linearity



Hisao Sato

3 MHz

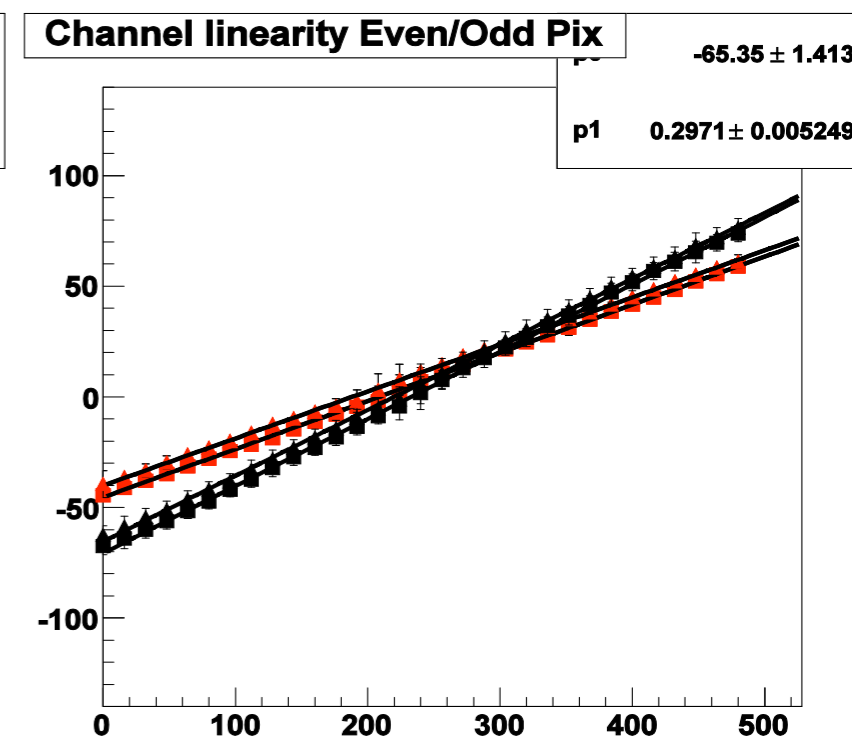
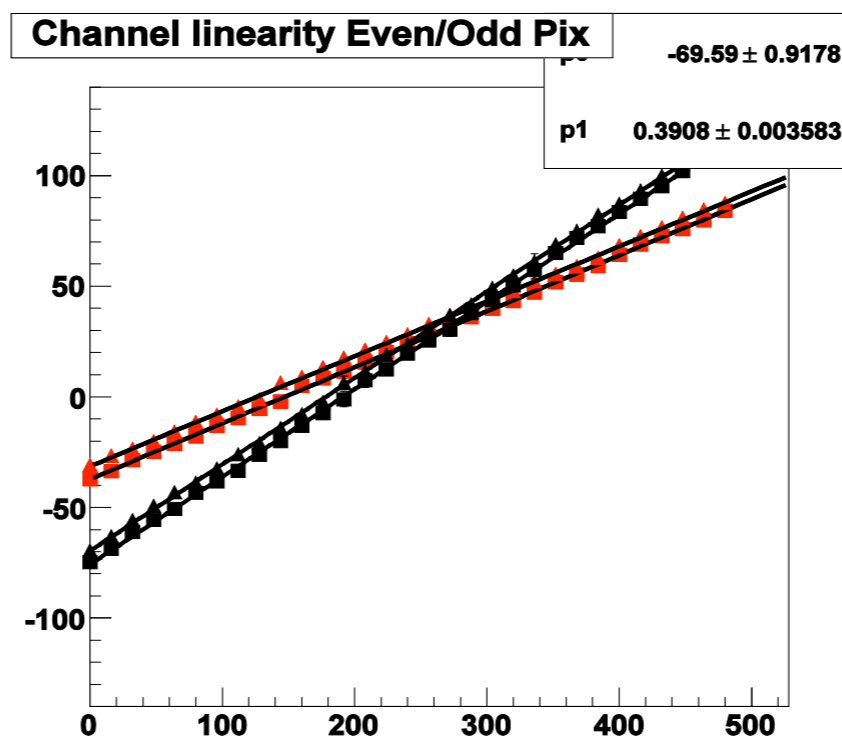
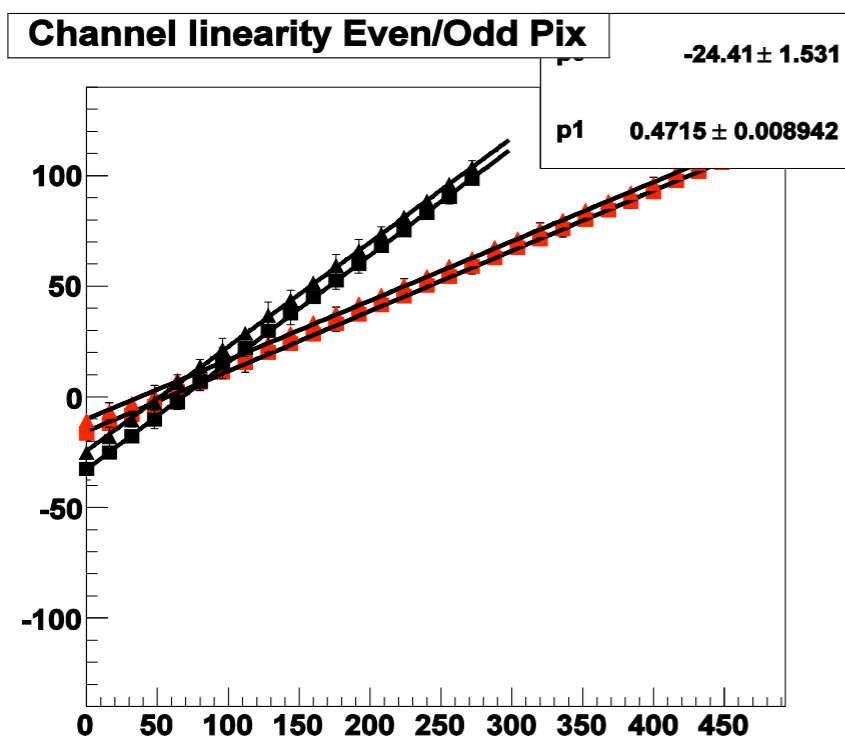
Gain : HIGH / LOW

50 MHz

Gain : HIGH / LOW

100 MHz

Gain : HIGH / LOW



Linearity looks reasonable, same result for all channels.



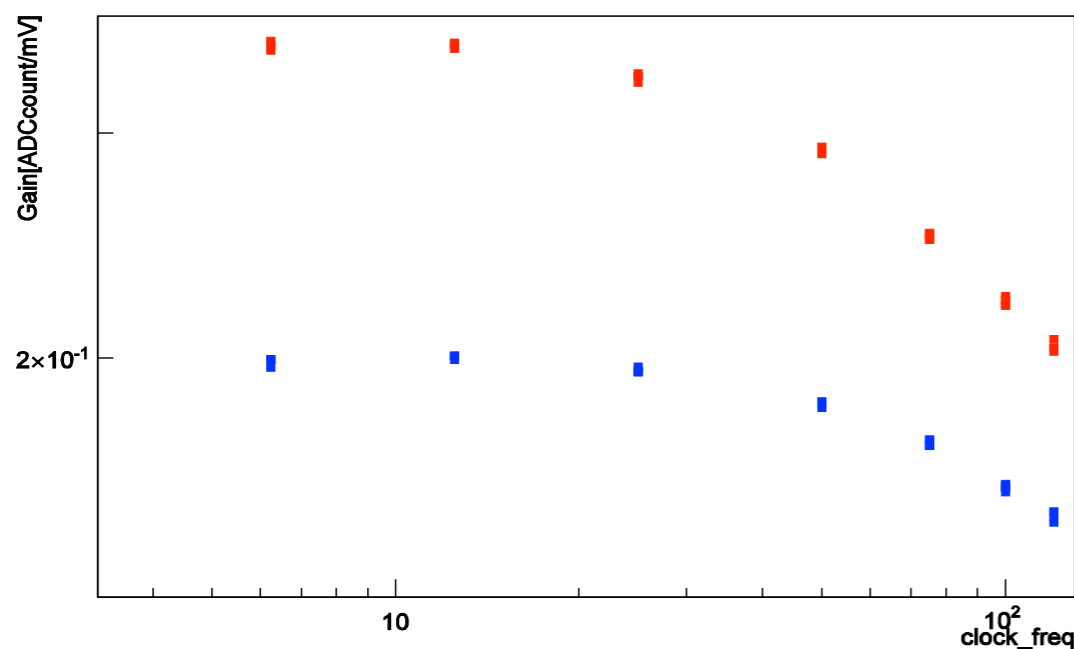
# Gain/ADC Sigma vs Frequency



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Gain vs Freq.

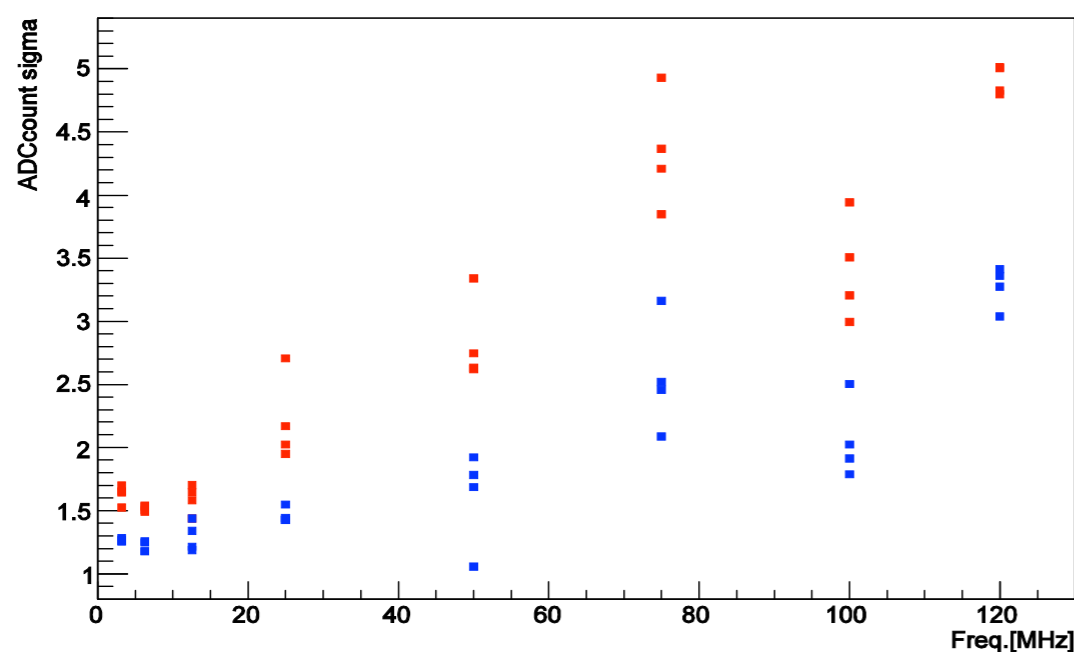


Channel 4-7

Gain [ADC count/mV] vs Freq [MHz]

Frequency dependency looks reasonable.  
It may need optimization.

hdist\_eve\_gaus\_p2:clock\_freq



Channel 4-7

Sigma [ADC count] vs Freq [MHz]

Needs further study to reduce noise.



# Challenges And Plans



- Presented status of CCD and ASIC tests.
- We tested successfully ASIC prototype 2 with 12um CCD.
- Successfully migrated to SEABAS2 based new test system.
- AFFROC characterization is going on.
- Power consumption goal of AFFROC is achieved.
- Frequency dependency of gain looks reasonable.
- We have just started looking into frequency dependence of noise which doesn't look reasonable, it worsens at higher frequencies.
- Other than noise, so far no major problem has been seen in AFFROC.
- Fe55 test with 6um CCD will be done soon (before year end). all setup is ready. Just have to take data.



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# BACKUP

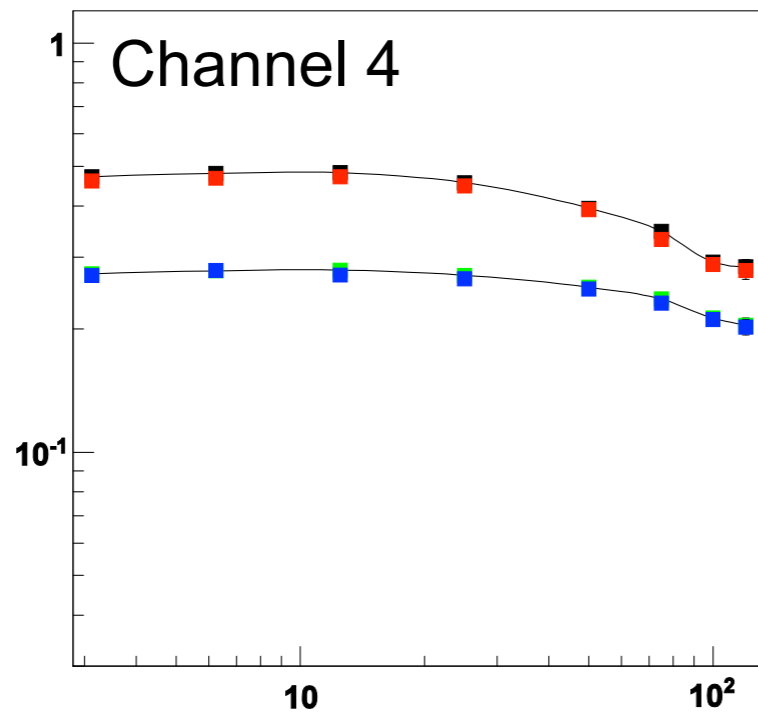




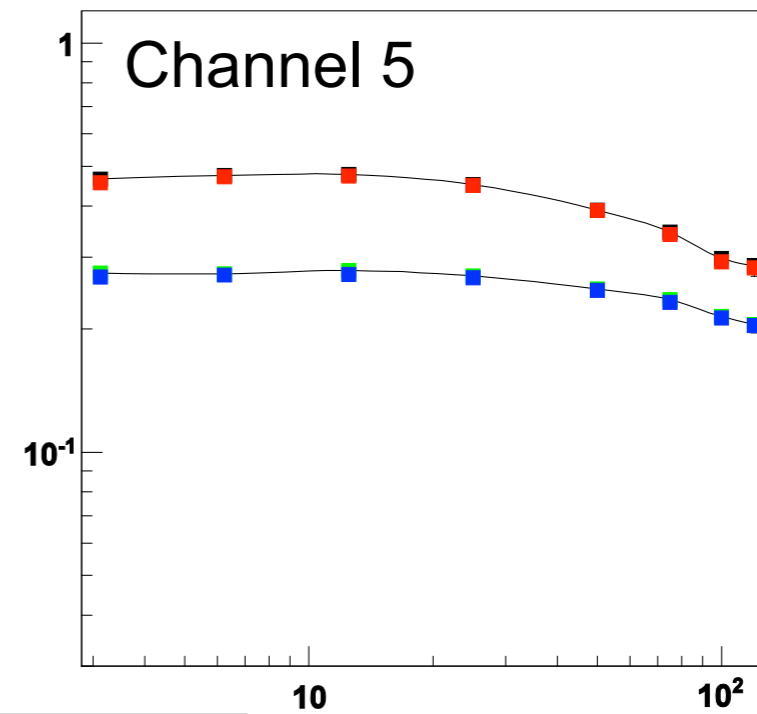
# Gain vs Frequency



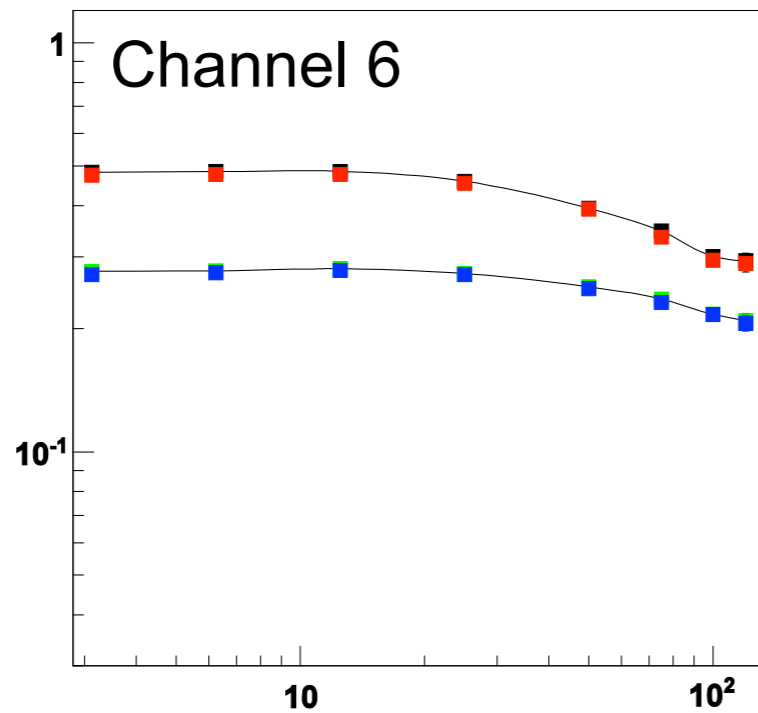
Freq vs Gain



Freq vs Gain



Freq vs Gain



Freq vs Gain

